



# What Limits the Performance of Wide Bandgap Cu(In,Ga)S<sub>2</sub> Solar Cells ?

UNSW SPREE Seminar, May 2022

Sudhanshu Shukla Senior Researcher at IMEC Belgium Formerly at <u>University of Luxembourg</u>

## **Climate EMERGENCY**



#### Response : Shift from fossil fuels to renewables

#### Carbon neutral and circular economy : Solar will be a major player



"I'd put my money on the sun and solar energy. What a source of power! I hope we don't have to wait till oil and coal run out before we tackle that" – **Thomas Edison** 

### Utilization of solar spectrum : Efficient light absorption



### Why Wide band-gap cells ? : Cu(In,Ga)S<sub>2</sub>



### Outline



#### Pure Sulfide Cu(In,Ga)S<sub>2</sub> ( $E_g$ : 1.5 – 2.4 eV) Low efficiency compared to CIGSe!



# Interface passivation



#### Path forward

- Higher quasi-Fermi level splitting
- Longer carrier lifetimes
- Improved carrier collection
- Growth on TCOs

### $V_{oc}$ deficit with increasing bandgap : Plateaus



#### Photovoltage Deficit



Appl. Phys. Lett. 80, 2598, 2002

# Before Cu(In,Ga)S<sub>2</sub>: CuInS<sub>2</sub>

Remain limited by deep defects (two) and near interface defects



### Cu(In,Ga)S<sub>2</sub> Solar Cells



UNSW SPREE Talk, May 2022

### **Open QUESTIONS**

- What limits the  $V_{oc}$  in CIGS solar cells  $\rightarrow$  Bulk as well as interface
- What are the deep defects in CIGS ? How can it be passivated ?
- How to fix interface recombination losses in CIGS ?

#### Absorber growth : Co-evaporation





GGI : [Ga]/[Ga+In] ~ 0.12 - 0.18



Structure and topography



### Cu-rich and Cu-poor CIGS



### Deep defect : DI and D2



Two dominant deep defects at ~ 200 meV (D1) and 500 meV (D2) far from the band-edge

## Cathodoluminescence : Band-edge and defect emission





Higher band-edge emission and lower defect band emission for Cu-poor absorbers

### Lower $V_{oc}$ deficit for Cu-poor CIGS





Thinking about even more Cu-poor films ? : OVCs

Shukla, Sood et al., Joule, 5, 1, 2021

Sudhanshu.shukla@imec.be

#### Interface losses





# So, what are these defects ?

#### Defect Formation Energies : Ab-initio calculations







#### Deep defects : Anti-site defects





- Acceptor like Cu<sub>In</sub> and Cu<sub>Ga</sub> have the lowest formation energy in Cu-rich domain → killer defects
- Donor like In<sub>Cu</sub> and Ga<sub>Cu</sub> defects have low formation energy in Cu-poor domain → compensation ?
- More Cu-poor CIGS : Think about defect complexes V<sub>Cu</sub> + (In<sub>Cu</sub> + Ga<sub>Cu</sub>)

# Charge carrier lifetime





CIGS/Zn(O,S) :  $\tau_1$ : 0.6 ns and  $\tau_2$ : 4.5 ns

High non-radiative recombination - Deep defects must be passivated



Shukla, Sood et al., Joule, 5, 1, 2021

22

#### Best solar cell performance



# Reduced $V_{oc}$ deficit



#### Current status



### What's next ? A possible roadmap



່ເມງອ

### Projects involving higher E<sub>g</sub> materials











Prof. Susanne Siebentritt Dr. Mohit Sood Damilola Adeleye LPV group

Prof. Rachel Oliver Dr. Gunnar Kusch Prof. Geoffroy Hautier Gian-Marco Rignanese

Reduce your carbon footprint

Dr. Nathalie Valle Dr. Brahime El Adib

Thank you for your attention

**LINEC** Prof. Bart Vermang

Fonds National de la <mark>Recherche</mark> Luxembourg